
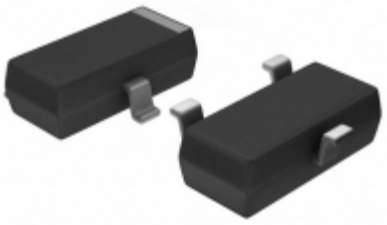
	<p>SI2301BDS-T1-E3</p>
	<p>Hersteller-Teilenummer: SI2301BDS-T1-E3</p> <hr/> <p>Hersteller / Marke: Vishay / Siliconix</p> <hr/> <p>Teil der Beschreibung: MOSFET P-CH 20V 2.2A SOT23-3</p> <hr/> <p>Datenblätter:  SI2301BDS-T1-E3.pdf</p> <hr/> <p>RoHs Status: Bleifrei / RoHS-konform</p> <hr/> <p>Lagerzustand: New original, 253114 pcs Stock Available.</p> <hr/> <p>Liefern von: Hong Kong</p> <hr/> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
	
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SI2301BDS-T1-E3
Hersteller	Vishay / Siliconix
Beschreibung	MOSFET P-CH 20V 2.2A SOT23-3
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	253114 pcs Stock
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	TO-236-3, SC-59, SOT-23-3
Supplier Device-Gehäuse	SOT-23-3 (TO-236)
Verlustleistung (max)	700mW (Ta)
Typ FET	P-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	20V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	2.2A (Ta)
Rds On (Max) @ Id, Vgs	100 mOhm @ 2.8A, 4.5V
VGS (th) (Max) @ Id	950mV @ 250µA
Gate Charge (Qg) (Max) @ Vgs	10nC @ 4.5V
Eingabekapazität (Ciss) (Max) @ Vds	375pF @ 6V
Antriebsspannung (Max Rds On, Min Rds On)	2.5V, 4.5V
Vgs (Max)	±8V
Verpackung	Tape & Reel (TR)

SI2301BDS-T1-E3 ist neu im Original, Suche SI2301BDS-T1-E3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI2301BDS-T1-E3 Vishay / Siliconix mit Garantie und Vertrauen. Anfrage SI2301BDS-T1-E3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SI2301BDS VISHAY SI2301BDS VISHAY</p>	 <p>SI2301BDS-T1-GE3 Electro-Films (EFI) / Vishay MOSFET P-CH 20V 2.2A SOT23-3</p>	 <p>SI2301BDS-T-E3 VISHAY VISHAY SOT-23</p>	 <p>SI2301BDS-T1 VISHAY SI2301BDS-T1 VISHAY</p>
 <p>SI2301BDS-TI-E3 Vishay Precision Group SI2301BDS-TI-E3 VISHAY</p>	 <p>SI2301BDS-T1-ES VISHAY VISHAY SOT23</p>	 <p>SI2301BDS-T1-GE3 Vishay / Siliconix MOSFET P-CH 20V 2.2A SOT23-3</p>	 <p>SI2301BDS-T1-E3 Electro-Films (EFI) / Vishay MOSFET P-CH 20V 2.2A SOT23-3</p>

heiße Teile

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|--------------------|--------------------|--------------------|--------------------|--------------------|
| ⊛ SI2172-A20-GMR | ↔ SI2173-A30-GMR | ➔ SI2173-A40-ZM7R | D SI2176-B30-GMR | ➔ SI2176-B30-ZM7R |
| ⊣ SI2176-B30-ZM8R | ⊛ SI2178-A20-GMR | D SI2191-A20-ZM7R | ➔ SI2196-A0A-GMR | ➔ SI2300/AE9T |
| ⊛ SI2300BDS-T1-GE3 | ⊣ SI2300DS | ⊛ SI2300DS-T1 | ↔ SI2300DS-T1-E3 | ➔ SI2300DS-T1-GE3 |
| D SI2300DS-T1-GE3 | ⊛ SI2300DS-TI-E3 | ⊣ SI2301-TP | ⊛ SI2301A1SHB | ➔ SI2301ADS |
| ➔ SI2301ADS-T1-E3 | ↔ SI2301ADS-T1-GE3 | ⊛ SI2301BDS | ⊣ SI2301BDS-E3 | ➔ SI2301BDS-T1 |
| ↔ SI2301BDS-T1-E3 | ➔ SI2301BDS-T1-GE3 | D SI2301BDS-T1-GE3 | ⊛ SI2301CDS | ⊣ SI2301CDS-T1-E3 |
| ⊛ SI2301CDS-T1-E3 | D SI2301CDS-T1-GE3 | ➔ SI2301CDS-T1-GE3 | ↔ SI2301DS | ➔ SI2301DS-E3 |
| ⊣ SI2301DS-T1 | ⊛ SI2301DS-T1-E3 | ↔ SI2301DS-T1-GE3 | ➔ SI2302ADS | ➔ SI2302ADS-T1 |
| ⊛ SI2302ADS-T1 | ⊣ SI2302ADS-T1-E3 | ⊛ SI2302ADS-T1-E3 | D SI2302ADS-T1-GE3 | ➔ SI2302ADS-T1-GE3 |
| ↔ SI2302BDS-T1-E3 | ⊛ SI2302CDS-T1-E3 | ⊣ SI2302CDS-T1-E3 | ⊛ SI2302CDS-T1-GE3 | ➔ SI2302CDS-T1-GE3 |

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